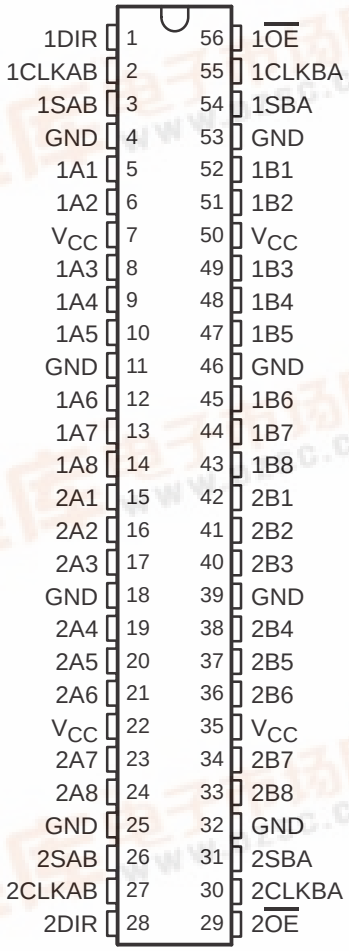
16-BIT BUS TRANSCEIVER AND REGISTER WITH 3-STATE OUTPUTS

SCAS318H – NOVEMBER 1993 – REVISED JUNE 1998

- **Member of the Texas Instruments *Widebus*™ Family**
- ***EPIC*™ (Enhanced-Performance Implanted CMOS) Submicron Process**
- **Typical V_{OLP} (Output Ground Bounce) < 0.8 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Typical V_{OHV} (Output V_{OH} Undershoot) > 2 V at V_{CC} = 3.3 V, T_A = 25°C**
- **Supports Mixed-Mode Signal Operation on All Ports (5-V Input/Output Voltage With 3.3-V V_{CC})**
- **Power Off Disables Outputs, Permitting Live Insertion**
- **ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)**
- **Latch-Up Performance Exceeds 250 mA Per JESD 17**
- **Bus Hold on Data Inputs Eliminates the Need for External Pullup/Pulldown Resistors**
- **Package Options Include Plastic 300-mil Shrink Small-Outline (DL) and Thin Shrink Small-Outline (DGG) Packages**

DGG OR DL PACKAGE
(TOP VIEW)



description

This 16-bit bus transceiver and register is designed for 1.65-V to 3.6-V V_{CC} operation.

The SN74LVCH16646A can be used as two 8-bit transceivers or one 16-bit transceiver. The device consists of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal registers.

Data on the A or B bus is clocked into the registers on the low-to-high transition of the appropriate clock (CLKAB or CLKBA) input. Figure 1 illustrates the four fundamental bus-management functions that can be performed with the SN74LVCH16646A.

Output-enable ($\overline{OE}$) and direction-control (DIR) inputs control the transceiver functions. In the transceiver mode, data present at the high-impedance port can be stored in either register or in both. The select-control (SAB and SBA) inputs can multiplex stored and real-time (transparent mode) data. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. DIR determines which bus receives data when $\overline{OE}$ is low. In the isolation mode ($\overline{OE}$ high), A data can be stored in one register and/or B data can be stored in the other register.

description (continued)

When an output function is disabled, the input function is still enabled and can be used to store and transmit data. Only one of the two buses, A or B, can be driven at a time.

Inputs can be driven from either 3.3-V or 5-V devices. This feature allows the use of these devices as translators in a mixed 3.3-V/5-V system environment.

To ensure the high-impedance state during power up or power down, $\overline{OE}$ should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

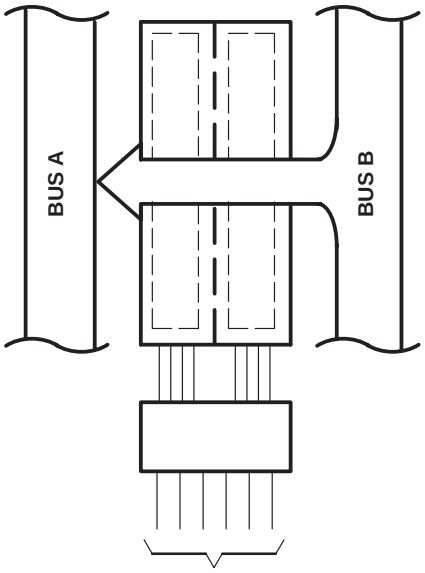
Active bus-hold circuitry holds unused or floating data inputs at a valid logic level.

The SN74LVCH16646A is characterized for operation from –40°C to 85°C.

FUNCTION TABLE

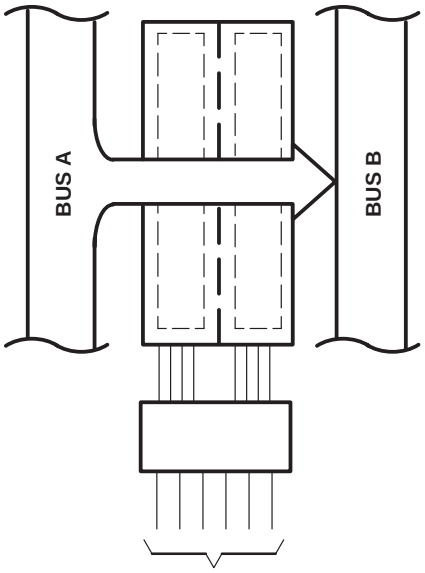
INPUTS						DATA I/O†		OPERATION OR FUNCTION
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA	A1–A8	B1–B8	
X	X	↑	X	X	X	Input	Unspecified	Store A, B unspecified†
X	X	X	↑	X	X	Unspecified	Input	Store B, A unspecified†
H	X	↑	↑	X	X	Input	Input	Store A and B data
H	X	H or L	H or L	X	X	Input	Input	Isolation, hold storage
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
L	H	X	X	L	X	Input	Output	Real-time A data to B Bus
L	H	H or L	X	H	X	Input	Output	Stored A data to bus

† The data-output functions may be enabled or disabled by various signals at $\overline{OE}$ or DIR. Data-input functions always are enabled, i.e., data at the bus terminals is stored on every low-to-high transition of the clock inputs.



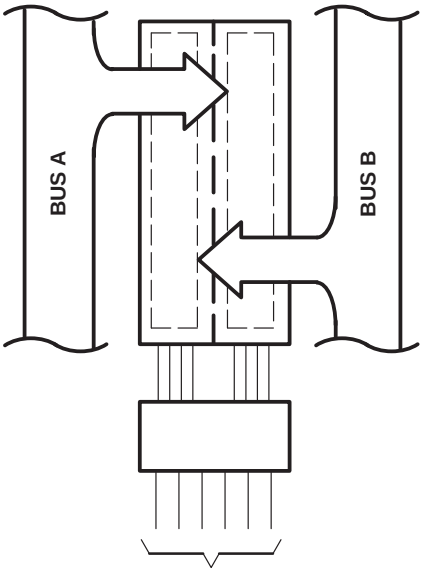
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



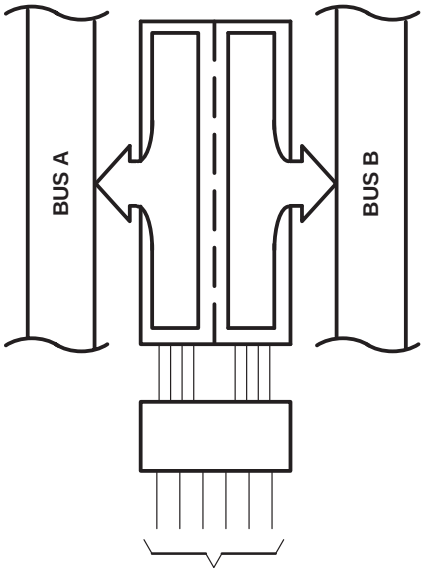
$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
X	X	↑	X	X	X
X	X	X	↑	X	X
H	X	↑	↑	X	X

STORAGE FROM
A, B, OR A AND B

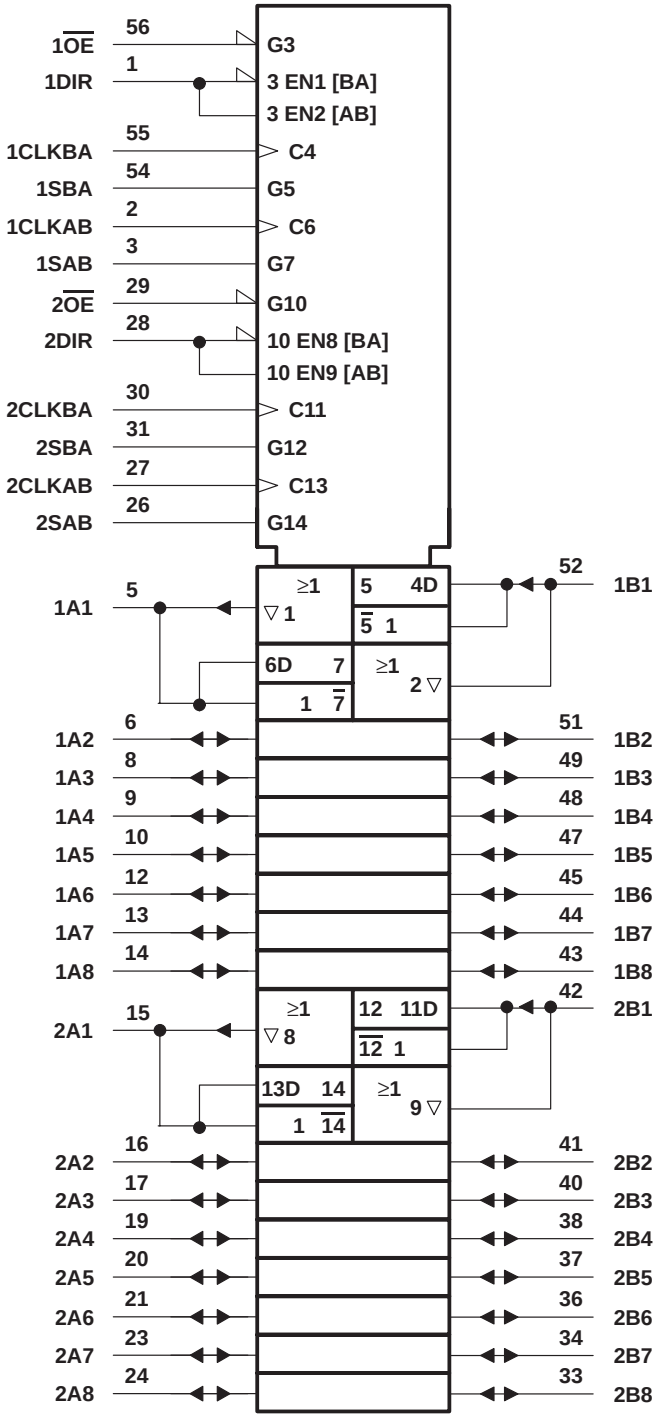


$\overline{OE}$	DIR	CLKAB	CLKBA	SAB	SBA
L	L	X	H or L	X	H
L	H	H or L	X	H	X

TRANSFER STORED DATA
TO A AND/OR B

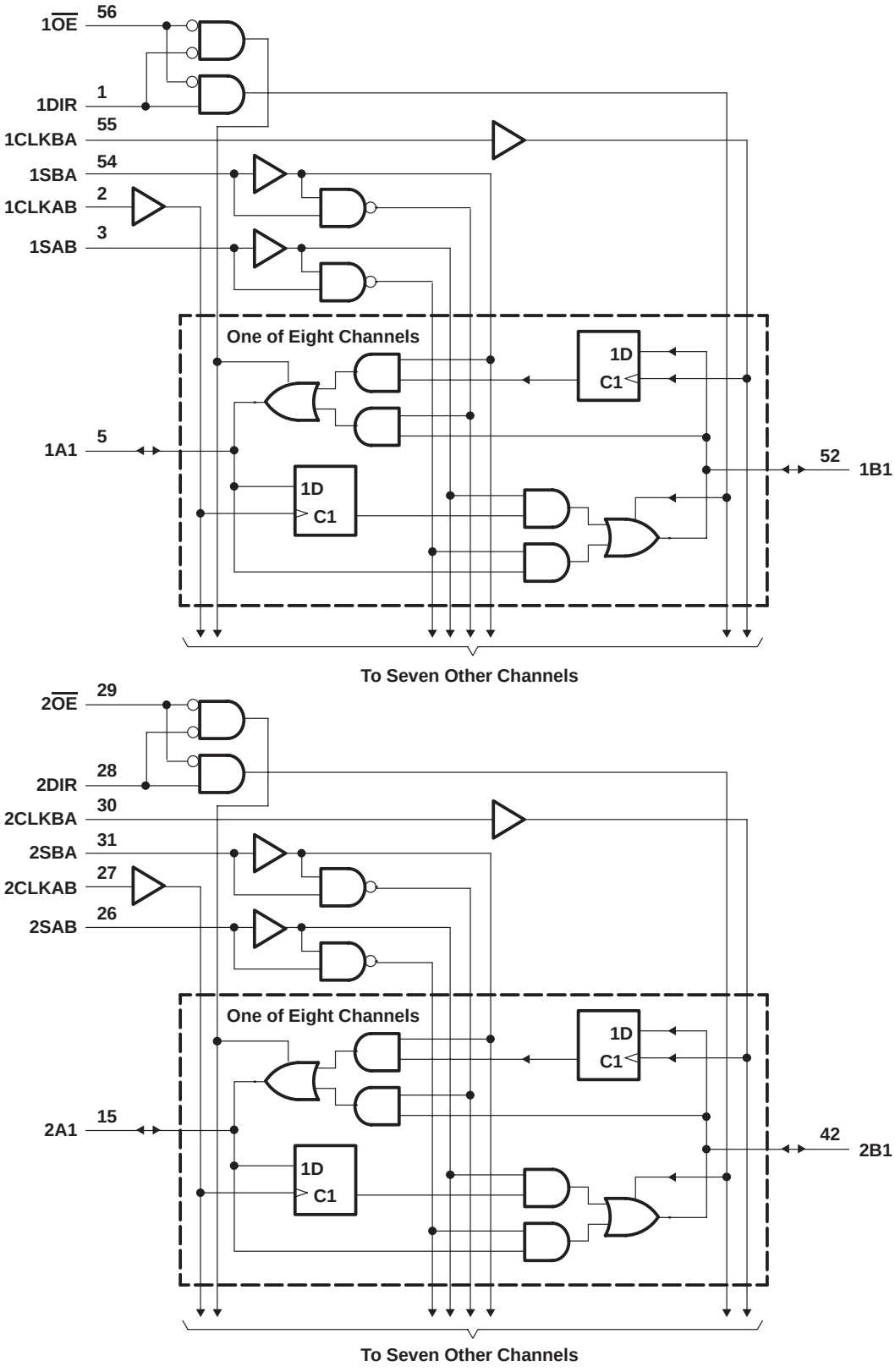
Figure 1. Bus-Management Functions

logic symbol†



† This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V_{CC} . . . . . –0.5 V to 6.5 V
Input voltage range, V_I: (see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high-impedance or power-off state, V_O
(see Note 1) . . . . . –0.5 V to 6.5 V
Voltage range applied to any output in the high or low state, V_O
(see Notes 1 and 2) . . . . . –0.5 V to V_{CC} + 0.5 V
Input clamp current, I_{IK} (V_I < 0) . . . . . –50 mA
Output clamp current, I_{OK} (V_O < 0) . . . . . –50 mA
Continuous output current, I_O . . . . . ±50 mA
Continuous current through each V_{CC} or GND . . . . . ±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DGG package . . . . . 81°C/W
DL package . . . . . 74°C/W
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
2. The value of V_{CC} is provided in the recommended operating conditions table.
3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT
V_{CC}	Supply voltage	Operating	1.65	3.6	V
		Data retention only	1.5		
V_{IH}	High-level input voltage	V_{CC} = 1.65 V to 1.95 V	0.65 × V_{CC}		V
		V_{CC} = 2.3 V to 2.7 V	1.7		
		V_{CC} = 2.7 V to 3.6 V	2		
V_{IL}	Low-level input voltage	V_{CC} = 1.65 V to 1.95 V		0.35 × V_{CC}	V
		V_{CC} = 2.3 V to 2.7 V		0.7	
		V_{CC} = 2.7 V to 3.6 V		0.8	
V_I	Input voltage		0	5.5	V
V_O	Output voltage	High or low state	0	V_{CC}	V
		3 state	0	5.5	
I_{OH}	High-level output current	V_{CC} = 1.65 V		–4	mA
		V_{CC} = 2.3 V		–8	
		V_{CC} = 2.7 V		–12	
		V_{CC} = 3 V		–24	
I_{OL}	Low-level output current	V_{CC} = 1.65 V		4	mA
		V_{CC} = 2.3 V		8	
		V_{CC} = 2.7 V		12	
		V_{CC} = 3 V		24	
$\Delta t/\Delta v$	Input transition rise or fall rate		0	10	ns/V
T_A	Operating free-air temperature		–40	85	°C

NOTE 4: All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP†	MAX	UNIT
V_{OH}		I_{OH} = –100 μA		1.65 V to 3.6 V	V_{CC}–0.2			V
		I_{OH} = –4 mA		1.65 V	1.2			
		I_{OH} = –8 mA		2.3 V	1.7			
		I_{OH} = –12 mA		2.7 V	2.2			
				3 V	2.4			
		I_{OH} = –24 mA		3 V	2.2			
V_{OL}		I_{OL} = 100 μA		1.65 V to 3.6 V			0.2	V
		I_{OL} = 4 mA		1.65 V			0.45	
		I_{OL} = 8 mA		2.3 V			0.7	
		I_{OL} = 12 mA		2.7 V			0.4	
		I_{OL} = 24 mA		3 V			0.55	
I_I	Control inputs	V_I = 0 to 5.5 V		3.6 V			±5	μA
$I_{I(hold)}$	A or B ports	V_I = 0.58 V		1.65 V	‡			μA
		V_I = 1.07 V			‡			
		V_I = 0.7 V		2.3 V	45			
		V_I = 1.7 V			–45			
		V_I = 0.8 V		3 V	75			
		V_I = 2 V			–75			
		V_I = 0 to 3.6 V§		3..6 V			±500	
I_{off}		V_I or V_O = 5.5 V		0			±10	μA
I_{OZ}¶		V_O = 0 to 5.5 V		3.6 V			±10	μA
I_{CC}		V_I = V_{CC} or GND	I_O = 0	3.6 V			20	μA
		3.6 V ≤ V_I ≤ 5.5 V#					20	
ΔI_{CC}		One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND		2.7 V to 3.6 V			500	μA
C_i	Control inputs	V_I = V_{CC} or GND		3.3 V		5		pF
C_{io}	A or B ports	V_O = V_{CC} or GND		3.3 V		8.5		pF

† All typical values are at V_{CC} = 3.3 V, T_A = 25°C.
‡ This information was not available at the time of publication.
§ This is the bus-hold maximum dynamic current required to switch the input from one state to another.
¶ For I/O ports, the parameter I_{OZ} includes the input leakage current, but not $I_{I(hold)}$.
# This applies in the disabled state only.

timing requirements over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figures 2 through 4)

		V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
		MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		‡		‡		150		150	MHz
t_w	Pulse duration, CLK high or low	‡		‡		3.3		3.3		ns
t_{su}	Setup time, A or B before CLKAB↑ or CLKBA↑	‡		‡		3.2		2.9		ns
t_h	Hold time, A or B after CLKAB↑ or CLKBA↑	‡		‡		0		0.3		ns

‡ This information was not available at the time of publication.

switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 2 through 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 1.8 V ± 0.15 V		V_{CC} = 2.5 V ± 0.2 V		V_{CC} = 2.7 V		V_{CC} = 3.3 V ± 0.3 V		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f_{max}			†		†		150		150		MHz
t_{pd}	A or B	B or A	†	†	†	†		6.8	1.3	5.7	ns
	CLKAB or CLKBA	A or B	†	†	†	†		7.9	1.8	6.7	
	SAB or SBA		†	†	†	†		9.2	1.7	7.7	
t_{en}	$\overline{OE}$	A or B	†	†	†	†		8.5	1.3	6.9	ns
t_{dis}			†	†	†	†		7.7	2.1	6.9	
t_{en}	DIR	A or B	†	†	†	†		8.5	1.4	7.2	ns
t_{dis}			†	†	†	†		7.8	2	7	

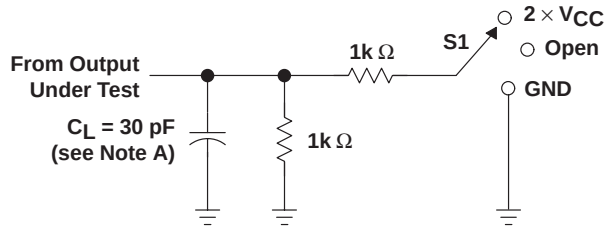
† This information was not available at the time of publication.

operating characteristics, T_A = 25°C

PARAMETER			TEST CONDITIONS	V_{CC} = 1.8 V ± 0.15 V	V_{CC} = 2.5 V ± 0.2 V	V_{CC} = 3.3 V ± 0.3 V	UNIT
				TYP	TYP	TYP	
C_{pd}	Power dissipation capacitance per transceiver	Outputs enabled	f = 10 MHz	†	†	60	pF
		Outputs disabled		†	†	12	

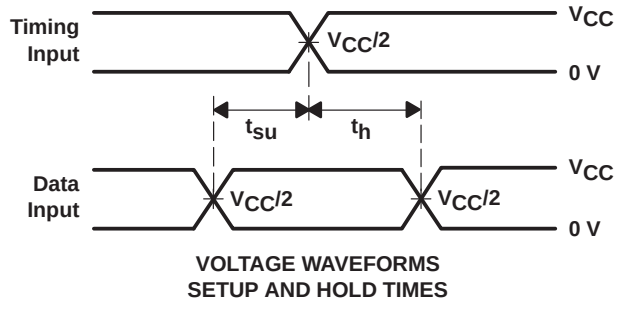
† This information was not available at the time of publication.

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 1.8 V ± 0.15 V

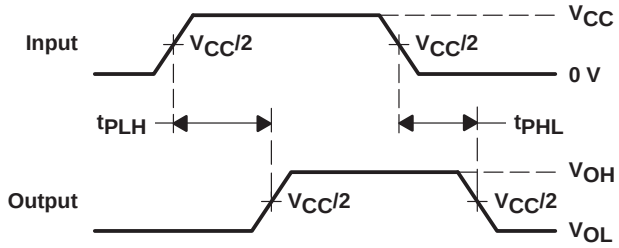


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	2 × V_{CC}
t_{PHZ}/t_{PZH}	Open

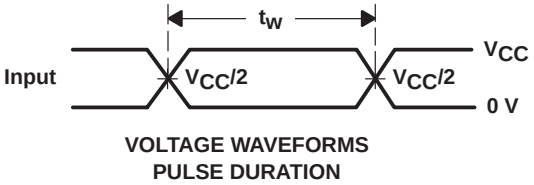
LOAD CIRCUIT



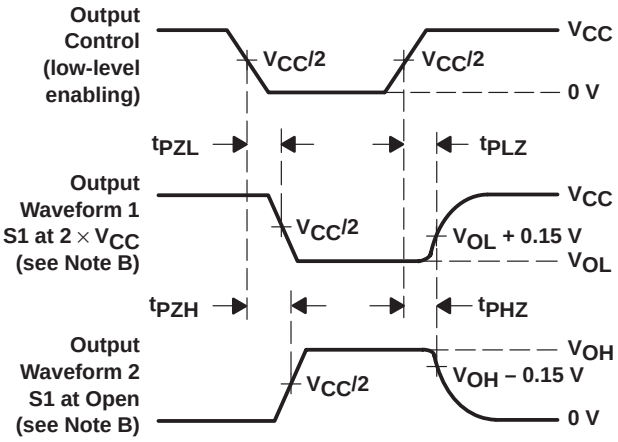
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION

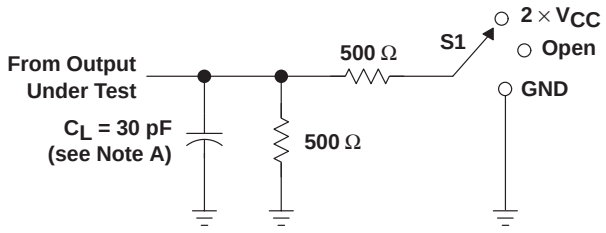


VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, Z_O = 50 Ω, t_r ≤ 2 ns, t_f ≤ 2 ns.
D. The outputs are measured one at a time with one transition per measurement.
E. t_{PLZ} and t_{PHZ} are the same as t_{dis}.
F. t_{PZL} and t_{PZH} are the same as t_{en}.
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

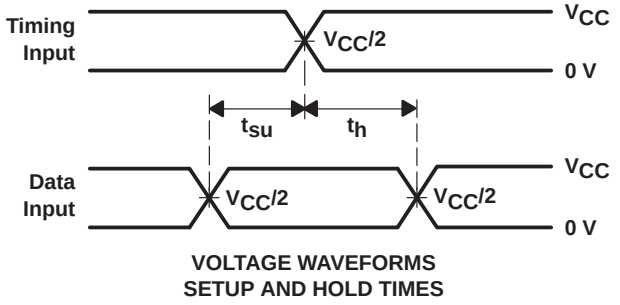
Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.5 V ± 0.2 V

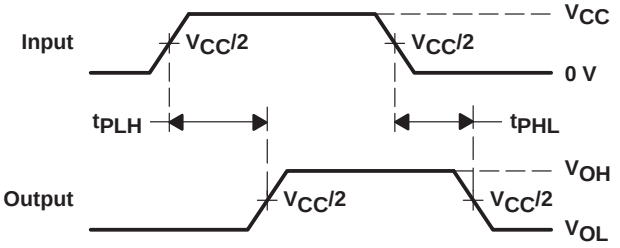


LOAD CIRCUIT

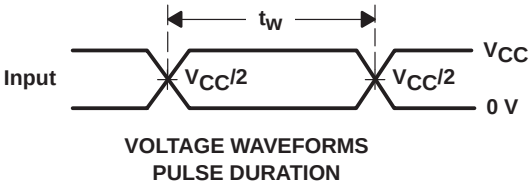
TEST	S1
t_{pd} t_{PLZ}/t_{PZL} t_{PHZ}/t_{PZH}	Open 2 × V_{CC} GND



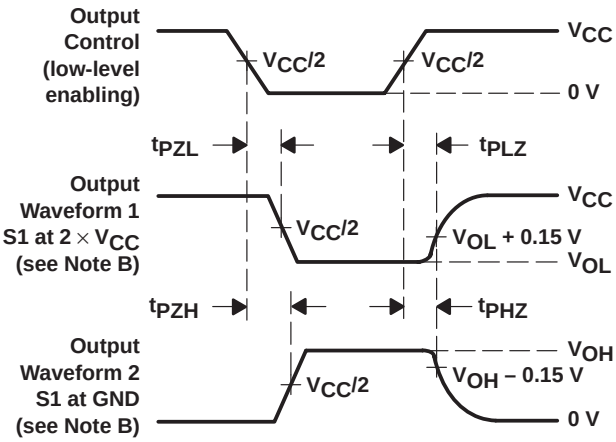
VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES



VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES

NOTES: A. C_L includes probe and jig capacitance.
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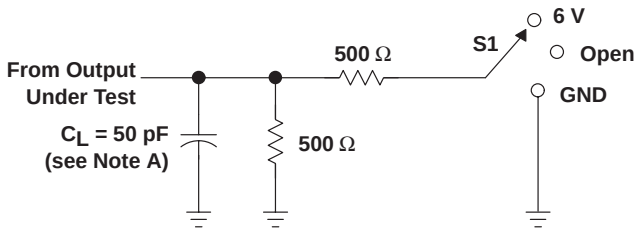
G. t_{PLH} and t_{PHL} are the same as t_{pd}.

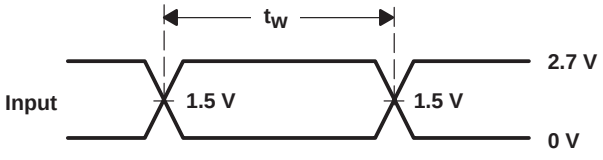
Figure 3. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION
V_{CC} = 2.7 V AND 3.3 V ± 0.3 V

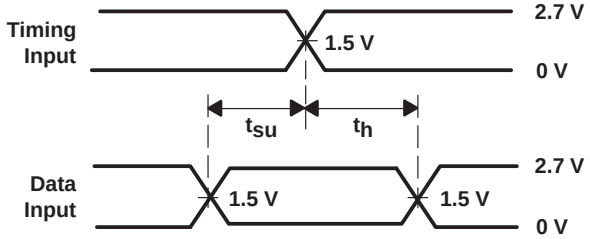


TEST	S1
t_{pd}	Open
t_{PLZ}/t_{PZL}	6 V
t_{PHZ}/t_{PZH}	GND

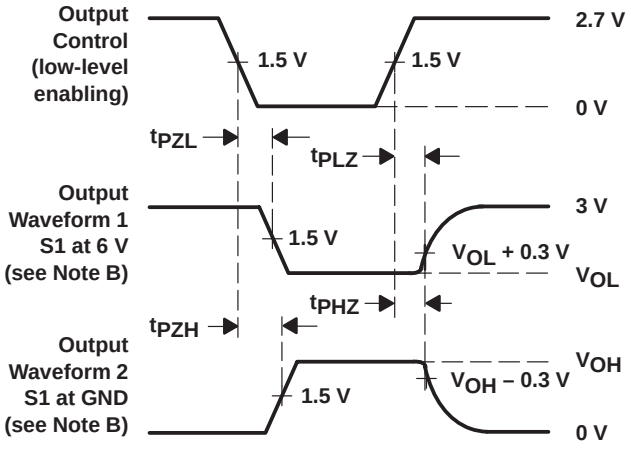
LOAD CIRCUIT



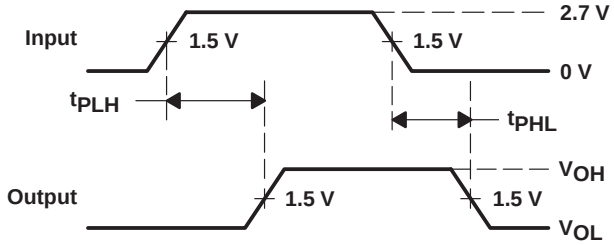
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES

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Figure 4. Load Circuit and Voltage Waveforms

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